ABSTRACT OF THE DISCLOSURE

A method of forming a via hole through a glass wafer includes depositing a material layer on an outer surface of the glass wafer, the material layer having a selection ratio higher than that of the glass wafer, forming a via-patterned portion on one side of the material layer, performing a first etching in which the via-patterned portion is etched to form a preliminary via hole, eliminating any remaining patterning material used in the formation of the via-patterned portion, performing a second etching in which the preliminary via hole is etched to form a via hole having a smooth surface and extending through the glass wafer, and eliminating the material layer. The method according to the present invention is able to form a via hole through a glass wafer without allowing formation of an undercut or minute cracks, thereby increasing the yield and reliability of MEMS elements.